

STB160N75F3 STP160N75F3 - STW160N75F3

N-channel 75V - 3.5mΩ - 120A - TO-220 - TO-247 - D²PAK STripFET™ Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)} (max.)	I _D
STB160N75F3	75V	$3.7~\text{m}\Omega$	120 A ⁽¹⁾
STP160N75F3	75V	4 mΩ	120 A ⁽¹⁾
STW160N75F3	75V	4 mΩ	120 A ⁽¹⁾

- 1. Current limited by package
- Ultra low on-resistance
- 100% Avalanche tested



■ Switching applications

Description

This N-channel enhancement mode Power MOSFET is the latest refinement of ST's STripFET™ process. The resulting transistor shows extremely high packing density for low on resistance, rugged avalanche characteristics and low gate charge.

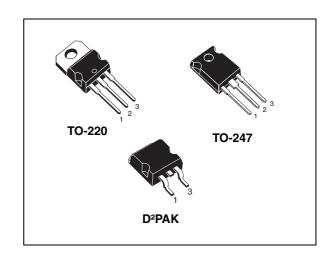


Figure 1. Internal schematic diagram

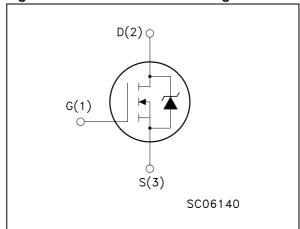


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB160N75F3	160N75F3	D²PAK	Tape & reel
STP160N75F3	160N75F3	TO-220	Tube
STW160N75F3	160N75F3	TO-247	Tube

October 2007 Rev 2 1/16

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	75	V
V _{GS}	Gate-source voltage	± 20	٧
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25°C	120	Α
I _D ⁽¹⁾	Drain current (continuous) at T _C = 100°C	120	Α
I _{DM} ⁽²⁾	Drain current (pulsed)	480	Α
P _{TOT}	Total dissipation at T _C = 25°C	330	W
	Derating factor	2.2	W/°C
dv/dt ⁽³⁾	Peak diode recovery voltage slope	20	V/ns
E _{AS} (4)	Single pulse avalanche energy	600	mJ
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

- 1. Current limited by package
- 2. Pulse width limited by safe operating area
- 3. $I_{SD} \leq 120 A, \ di/dt \leq 1100 \ A/\mu s, \ V_{DD} \leq 60 V, \ T_J \leq T_{JMAX}$
- 4. Starting $TJ = 25^{\circ}C$, $I_D = 60A$, $V_{DD} = 25V$

Table 3. Thermal resistance

Symbol	Parameter		Unit		
Symbol	Farameter	TO-220	TO-247	D²PAK	Oill
Rthj-case	Thermal resistance junction-case max		0.45		°C/W
Rthj-amb	Thermal resistance junction-ambient max	62.5	62.5 50		°C/W
Rthj-pcb ⁽¹⁾	Thermal resistance junction-pcb			50	°C/W
T _I	Maximum lead temperature for soldering purpose		300		°C

1. When mounted on 1 inch² FR4 2 oz Cu

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions		Min.	Тур.	Max	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$		75			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	$V_{DS} = Max rating,$ $V_{DS} = Max$ rating, @ 125°C				10 100	μΑ μΑ
I _{GSS}	Gate body leakage current (V _{DS} = 0)	$V_{GS} = \pm 20V$				±200	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2		4	٧
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 60A	TO-220 TO-247 D ² PAK		3.5 3.2	4 3.7	mΩ mΩ

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} =25V, f=1 MHz, V _{GS} =0		6750 1080 40		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} =37.5V, I_{D} = 120A V_{GS} =10V (see Figure 16)		85 27 26		nC nC nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} =37.5 V, I_{D} = 60A, R_{G} =4.7 Ω , V_{GS} =10V, (see Figure 18)		22 65 100 15		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				120 480	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} =120A, V _{GS} =0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I _{SD} =120A, V _{DD} = 20 V, di/dt = 100 A/µs, Tj=25°C (see Figure 17)		70 150 4.2		ns nC A

^{1.} Pulse with limited by safe operating area

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^{2.} Pulsed: pulse duration = $300\mu s$, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220 / Figure 3. Thermal impedance for TO-220 / TO-247

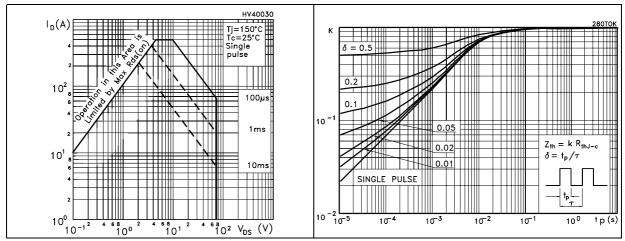


Figure 4. Safe operating area for D2PAK

Figure 5. Thermal impedance for D²PAK

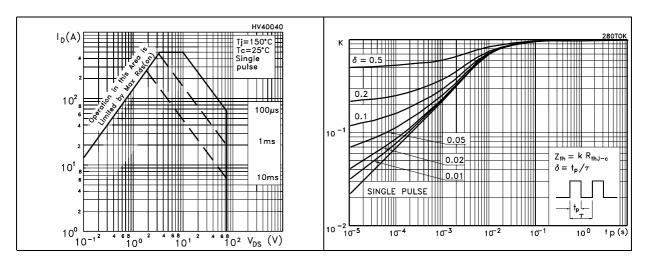
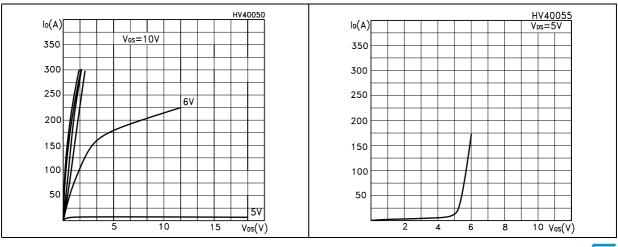


Figure 6. Output characteristics

Figure 7. Transfer characteristics



HV40080 R_{DS(on)} V(BR)DSS V_{GS}=0 $(m\Omega)$ (norm) lo=250µA 3.7 1.2 $V_{GS} = 10V$ 1.1 3.6 1.0 3.5 3.4 0.9 0.8 ō -50 50 100 TJ(°C) 30 60 90 120 $I_D(A)$

Figure 8. Normalized BV_{DSS} vs temperature Figure 9. Static drain-source on resistance

Figure 10. Gate charge vs gate-source voltage Figure 11. Capacitance variations

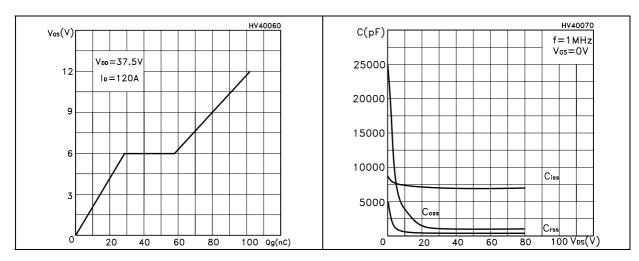


Figure 12. Normalized gate threshold voltage Figure 13. Normalized on resistance vs vs temperature temperature

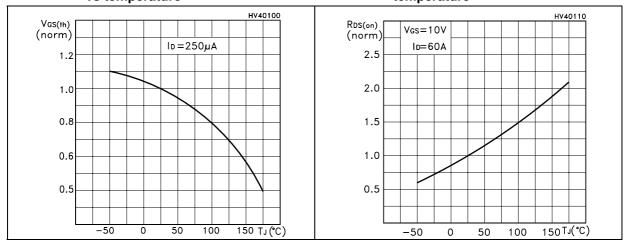
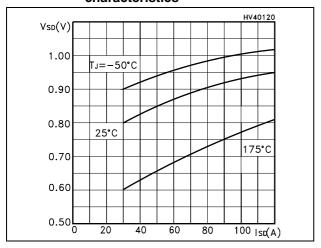


Figure 14. Source-drain diode forward characteristics



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3 Test circuit

Figure 15. Switching times test circuit for resistive load

Figure 16. Gate charge test circuit

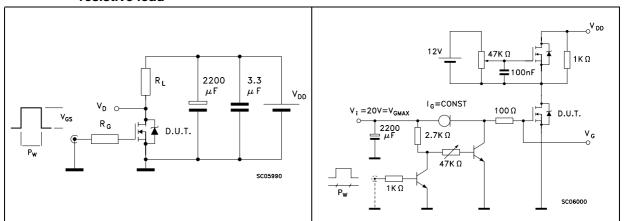


Figure 17. Test circuit for inductive load switching and diode recovery times

Figure 18. Unclamped inductive load test circuit

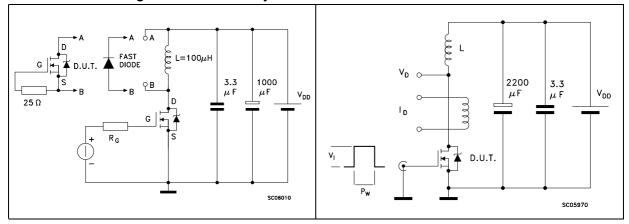
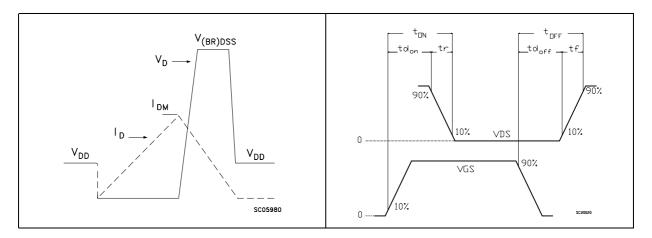


Figure 19. Unclamped inductive waveform

Figure 20. Switching time waveform

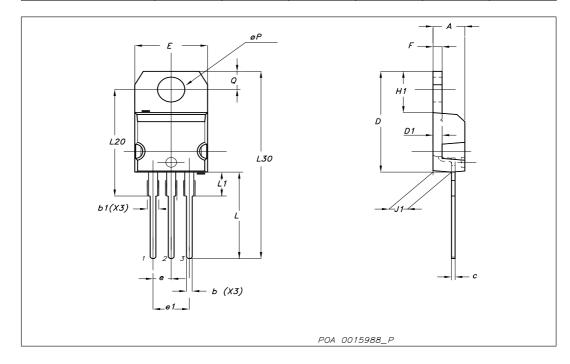


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

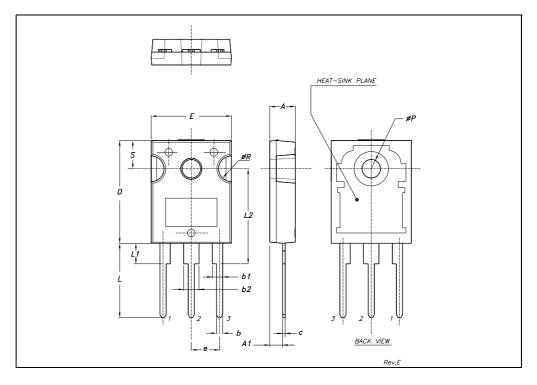
TO-220 mechanical data

Dim		mm			inch	
Dilli	Min	Тур	Max	Min	Тур	Max
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



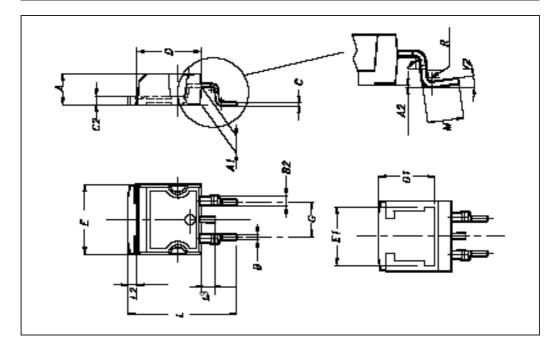
TO-247 MECHANICAL DATA

DIM.		mm.			inch	
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
С	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
е		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øΡ	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



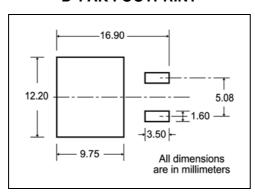
D²PAK mechanical data

Dim		mm			inch	
	Min	Тур	Max	Min	Тур	Max
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.50		0.55
L3	1.4		1.75	0.055		0.68
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

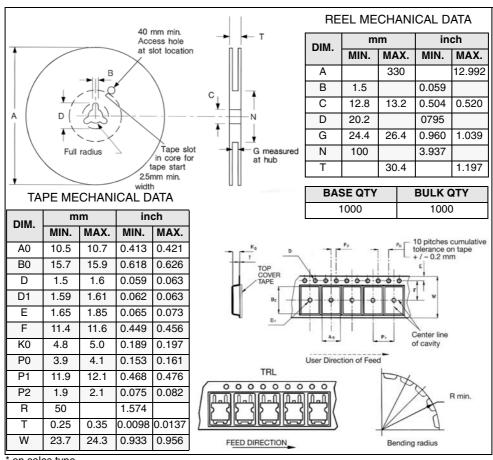


Packaging mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



on sales type

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
07-Feb-2007	1	First release
02-Oct-2007	2	New section has been added: Electrical characteristics (curves)

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